rfmd.com

# **RF1602**

### **BROADBAND SPDT SWITCH**

Package: QFN, 2mm x 2mm x 0.55mm

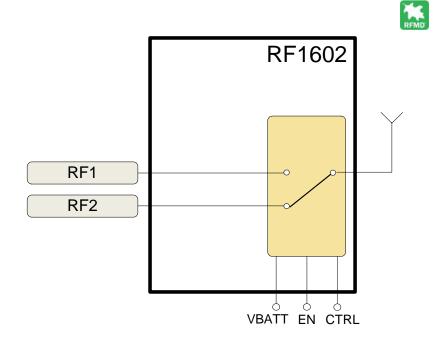


### **Features**

- Low Frequency to 3.5GHz Operation
- Low Insertion Loss, Typ. 0.3dB at 1GHz
- Very High Isolation, Typ. 42dB at 1GHz
- High Linearity, IIP2 Typ. 129dBm
- Direct Connection to V<sub>BATT</sub>
- Compatible with Low Voltage Logic (V<sub>HIGH</sub> Minimum = 1.3V)
- No External DC Blocking Capacitors Required on RF Paths Unless DC is applied Externally
- 2kV HBM Rating on All Ports

### **Applications**

- SV-LTE, WCDMA, GSM
- Post PA Switching
- General Purpose Switching Applications



Functional Block Diagram

### **Product Description**

The RF1602 is a single-pole dual-throw (SPDT) switch designed for switching applications requiring very low insertion loss and high power handling capability coupled with minimal DC power consumption. The excellent linearity performance achieved by the RF1602 makes it ideal for use in SV-LTE, WCDMA, and CDMA applications. The RF1602 offers very high isolation between RF ports providing greater separation between transmit and receive paths. The RF1602 is packaged in a very compact 2mm x 2mm x 0.55mm 12-Pin QFN package.

### **Ordering Information**

RF1602 Broadband SPDT Switch
RF1602PCBA-41X Fully Assembled Evaluation Board

Optimum Te	chnology	<b>Matching®</b>	Applied
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☐ GaAs HBT	☐ SiGe BiCMOS	☐_GaAs pHEMT	☐ GaN HEMT
☐ GaAs MESFET	☐ Si BiCMOS	▼ Si CMOS	☐ RF MEMS
☐ InGaP HBT	☐ SiGe HBT	☐ Si BJT	☐ LDMOS

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### **Absolute Maximum Ratings**

Parameter	Rating	Unit
Maximum V <sub>BATT</sub>	6.0	V
Maximum EN	3.0	V
Maximum CTRL	3.0	V
Maximum Power Handling (6:1 VSWR,Temp =25 °C )	+36	dBm
Operating Temperature	-30 to +85	°C
Storage Temperature	-40 to +125	°C



#### Caution! ESD sensitive device.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

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RFMD Green: RoHS compliant per EU Directive 2002/95/EC, halogen free per IEC 61249-2-21, < 1000 ppm each of antimony trioxide in polymeric materials and red phosphorus as a flame retardant, and <2% antimony in

Parameter	Specification			Unit	Condition
	Min.	Тур.	Max.	Offic	Condition
					(All Nominal Test Conditions Unless Otherwise Stated) $V_{BATT}$ = 3.5V, Temperature = 25 °C, All RF ports terminated in $50\Omega$
Insertion Loss					
RF1 to ANT, RF2 to ANT		0.30	0.40	dB	400MHz to 1GHz
		0.30	0.45	dB	1.0GHz to 2.0GHz
		0.35	0.50	dB	2.0GHz to 2.5GHz
		0.40	0.55	dB	2.5GHz to 3.5GHz
Isolation					
RF1 to RF2, RF2 to RF1	37	42		dB	400MHz to 1GHz
	31	34		dB	1.0GHz to 2.0GHz
	30	32		dB	2.0GHz to 2.5GHz
	25	29		dB	2.5GHz to 3.5GHz
RF Port Return Loss		II.	Ш		
ANT, RF1, RF2	10	15		dB	400MHz to 3.5GHz
900MHz Harmonics		II.	Ш		
Second Harmonic		-95	-75	dBc	P <sub>IN</sub> = 35dBm
Third Harmonic		-90	-75	dBc	
1800MHz Harmonics	·	li .			
Second Harmonic		-95	-75	dBc	P <sub>IN</sub> =33dBm
Third Harmonic		-90	-75	dBc	
IIP2	+	!	+	+	
RF1, RF2, ANT (Cell)	122	129		dBm	Tone 1: 836.5MHz at +26dBm Tone 2: 1718MHz at -20dBm Receive Freq: 881.5MHz
RF1, RF2, ANT (AWS)	122	129		dBm	Tone 1: 1732.5MHz at +26dBm Tone 2: 3865MHz at -20dBm Receive Freq: 2132.5MHz
RF1, RF2, ANT (PCS)	122	129		dBm	Tone 1: 1880MHz at +26dBm Tone 2: 3840MHz at -20dBm Receive Freq: 1960MHz
RF1, RF2, ANT (IMT)	122	129		dBm	Tone 1: 1950MHz at +26dBm Tone 2: 4090MHz at -20dBm Receive Freq: 2140MHz



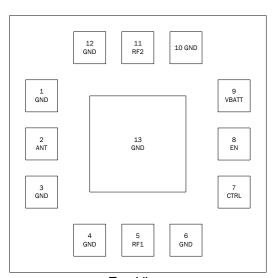
Parameter	Specification			Hoit	Condition
raiailletei	Min.	Тур.	Max.	Unit	Condition
IP3 SV-LTE					
RF1, RF2, ANT (Cell)		83		dBm	Tone 1: 786MHz at +23dBm Tone 2: 825MHz at +14dBm Receive Freq: 747MHz
RF1, RF2, ANT (Cell)		80		dBm	Tone 1: 782MHz at +23dBm Tone 2: 827MHz at +14dBm Receive Freq: 872MHz
IP3		1			
RF1, RF2, ANT (Cell)	70	75		dBm	Tone 1: 836.5MHz at +26dBm Tone 2: 791.5MHz at -20dBm Receive Freq: 881.5MHz
RF1, RF2, ANT (IMT)	70	75		dBm	Tone 1: 1950MHz at +26dBm Tone 2: 1760MHz at -20dBm Receive Freq: 2140MHz
Max Operating Power					
			36	dBm	$50\Omega$ , Temp = $25$ °C
			35	dBm	VSWR = 6:1, Temp = -30° to +85°C
Supply and Control Signal Characteri	stics				
Supply Voltage, V <sub>BATT</sub>	2.7	3.5	4.6	V	
Supply Current, V <sub>BATT</sub>					
EN = HIGH		100	200	μА	
EN = LOW		14	20	μΑ	
Control Voltage (EN, CTRL)					
$V_{HIGH}$	1.3	1.8	2.7	V	
$V_{LOW}$		0	0.45	V	
Control Current					
I <sub>HIGH</sub>		2.5	5	μΑ	
I <sub>LOW</sub>		1	3	μΑ	
Switching Time		I			
Switching Speed ON		2	5	μS	All combination; 50% control to 90% RF ON
Switching Speed RF OFF		2	5	μS	All combinations; 50% control to 10% RF OFF
Start Up Time from Shut- down			5	μs	Maximum set up time for the switch to reach fully compliant operation



## **Pin Names and Description**

Pin	Function	Description
1	GND	Ground.
2	ANT	Single ended RF port.
3	GND	Ground.
4	GND	Ground.
5	RF1	Single ended RF port.
6	GND	Ground.
7	CTRL	Switch logic control input.
8	EN	Switch logic control input, shutdown for low leakage current.
9	VBATT	Supply voltage from battery.
10	GND	Ground.
11	RF2	Single ended RF port.
12	GND	Ground.
13	Package Base	Ground.

### **Pin Out**



Top View

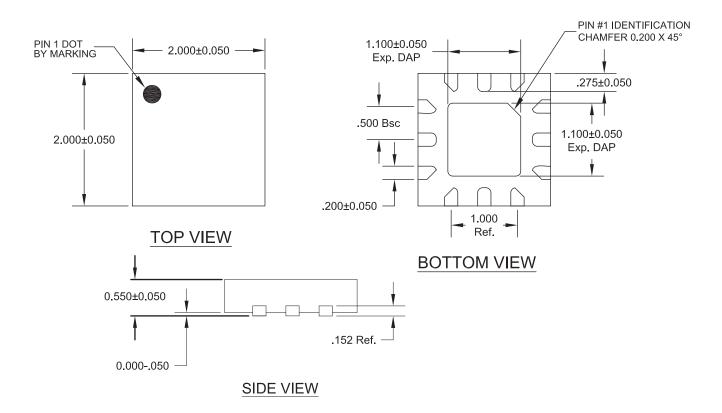
## **Control Logic**

State	V <sub>BATT</sub>	CTRL	EN	RF Path
1	2.7V to 4.6V	$V_{HIGH}$	V <sub>HIGH</sub>	ANT-RF2
2	2.7V to 4.6V	$V_{LOW}$	$V_{HIGH}$	ANT-RF1
Shutdown	2.7V to 4.6V	Don't Care	$V_{LOW}$	Shutdown

The switch is operable in 3 states. The switch is designed for two modes: active and shutdown. Assuming VBATT is always between 2.7V and 4.6V the switch is controlled by the EN voltage. When EN is HIGH the switch is active and when EN is LOW the switch is in standby mode.



# **Package Drawing**



# **RF1602**



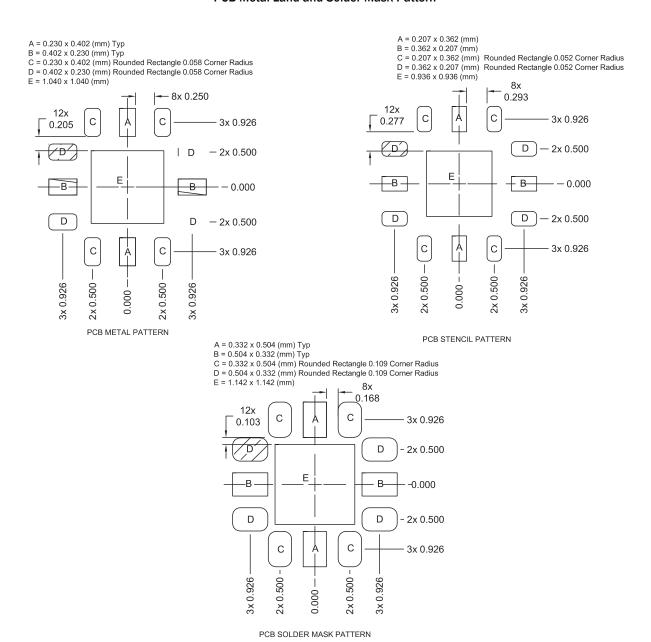
#### **PCB Surface Finish**

The PCB surface finish used for RFMD's qualification process is electroless nickel, immersion gold. Typical thickness is  $3\mu$ inch to  $8\mu$ inch gold over  $180\mu$ inch nickel.

#### **PCB Land Pattern Recommendation**

PCB land patterns for RFMD components are based on IPC-7351 standards and RFMD empirical data. The pad pattern shown has been developed and tested for optimized assembly at RFMD. The PCB land pattern has been developed to accommodate lead and package tolerances. Since surface mount processes vary from company to company, careful process development is recommended.

#### **PCB Metal Land and Solder Mask Pattern**



Shaded are represents Pin 1 location.



## **Evaluation Board Schematic**

